

Abstract

A semiconductor system (200) having a pn transition and a method for manufacturing a semiconductor system (200) are described. The semiconductor system (200) is designed in the form of a chip (10) having an edge region, the semiconductor system (200) includes a first layer (2) of a first conductivity type and a second layer (1) of a second conductivity type, which is of opposite polarity to the first conductivity type. The first layer (2) has an edge region (2a) and a center region (2b), the pn transition being provided between the first layer and the second layer (1). The second layer (2) is more weakly doped in its edge region (2a) than in its center region (2b), and the boundary surface (12) of the pn transition at the edge region (2a) is non-parallel to the main chip plane (13).